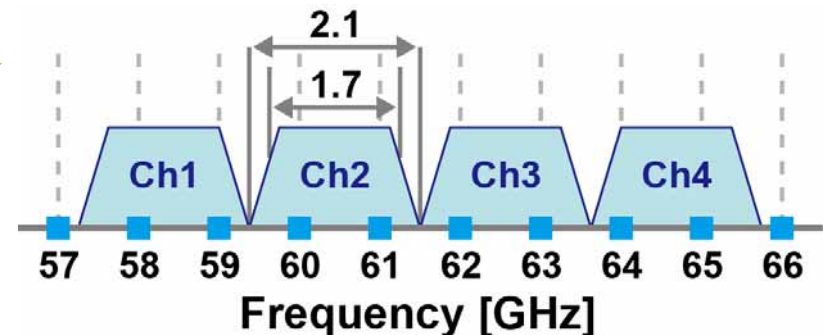
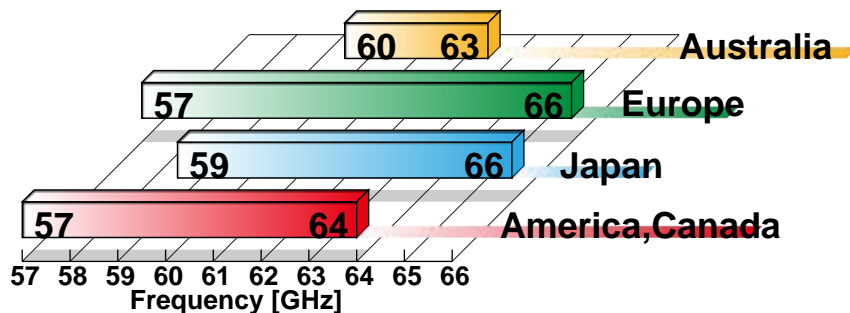


A 60GHz Direct-Conversion Transmitter in 65nm CMOS Technology

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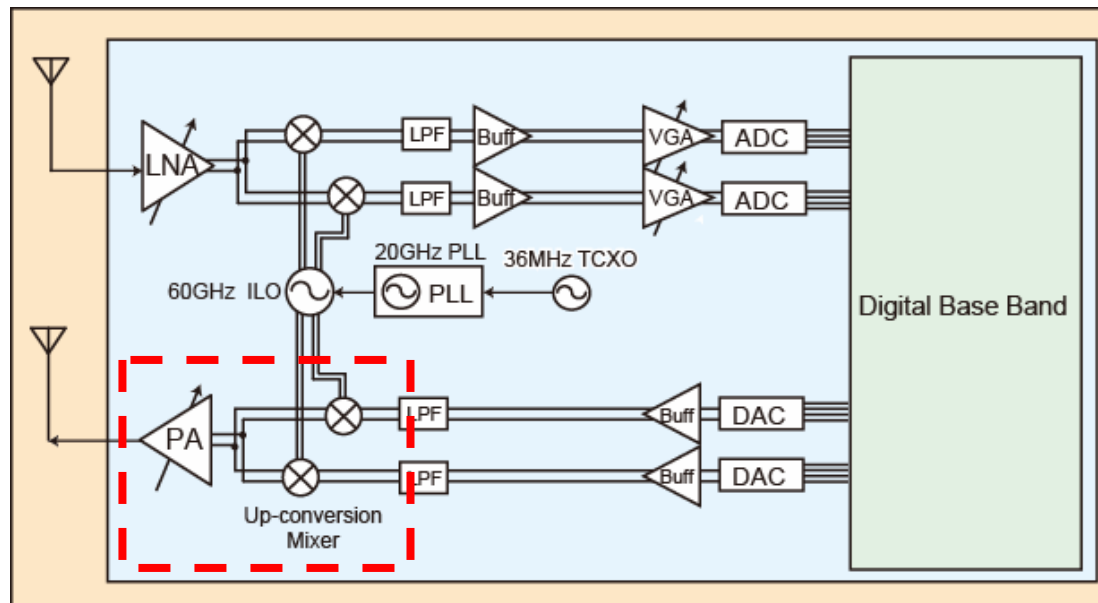
- **CMOS 60GHz RF Circuits**
 - Available wide frequency range without licenses
 - High data rate wireless communication
 - IEEE 802.15.3c
 - 1.7 GHz x 4 ch
 - QPSK : 14 Gbps, 16QAM : 28 Gbps



Available frequency range

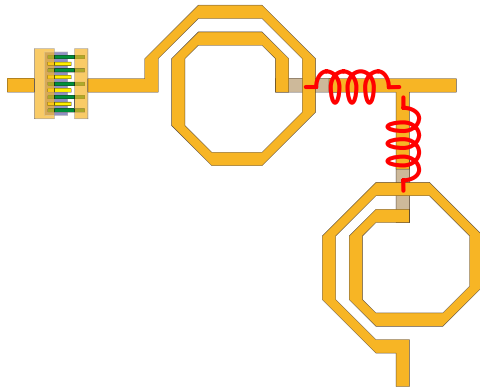
IEEE 802.15.3c

- **Direct conversion system**
 - **Power Amplifier**
 - **Up-conversion Mixer**

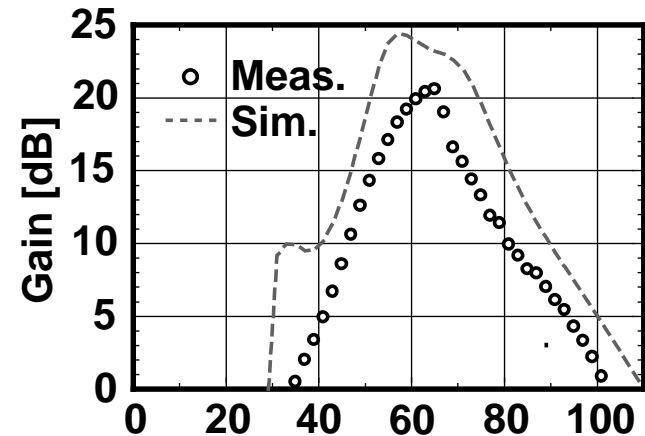


RF Front-end

- **Parasitic elements**
 - The present device models are not accurate at more than 20GHz.
 - Large error between sim. and meas.
 - Modeling of components is needed.
 - Transistors, Capacitors, TLs, Decoupling Cap.
 - A new de-embedding method is applied.

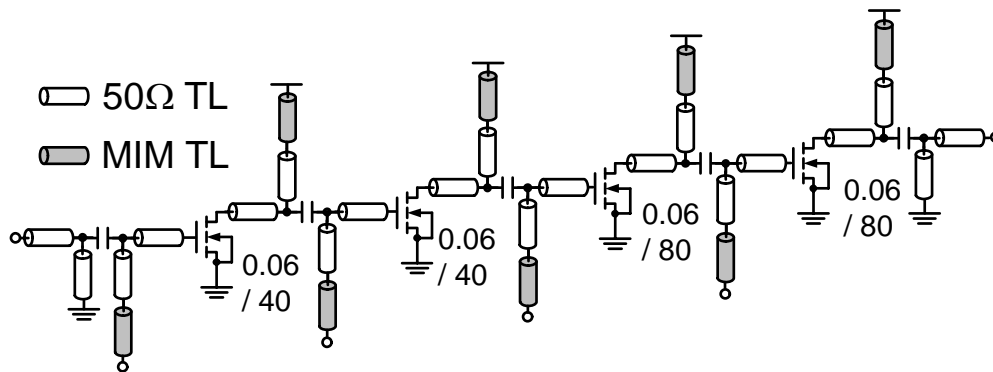


Parasitic elements

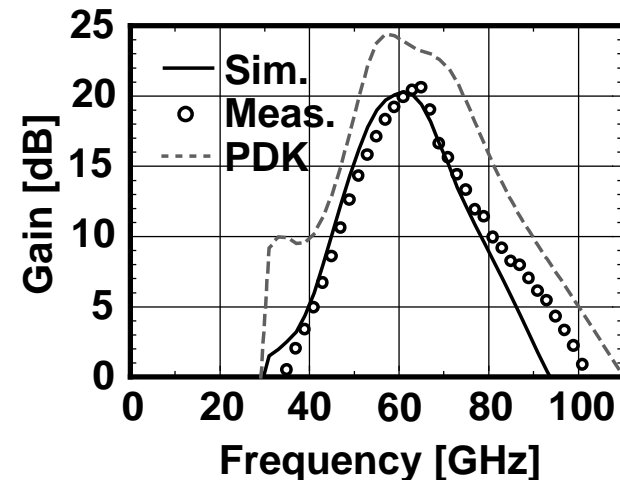


Gain of PA

- **Power Amplifier**
 - CMOS 65nm process
 - 4-stage PA
 - We used the device models we built.
- **Measurement results**
 - Simulation error reduced. 5 [dB] → 0.5 [dB]

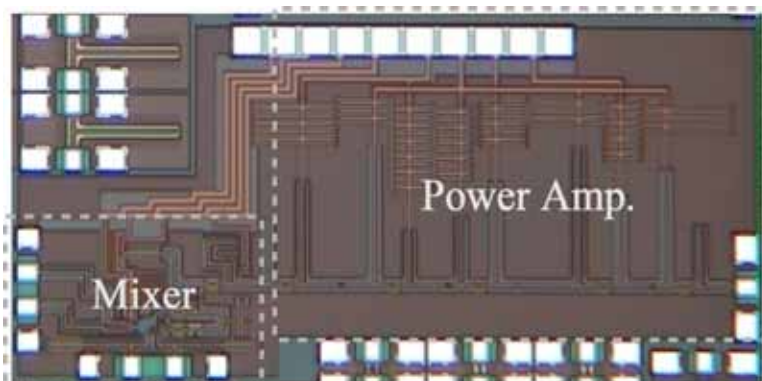


PA Schematic

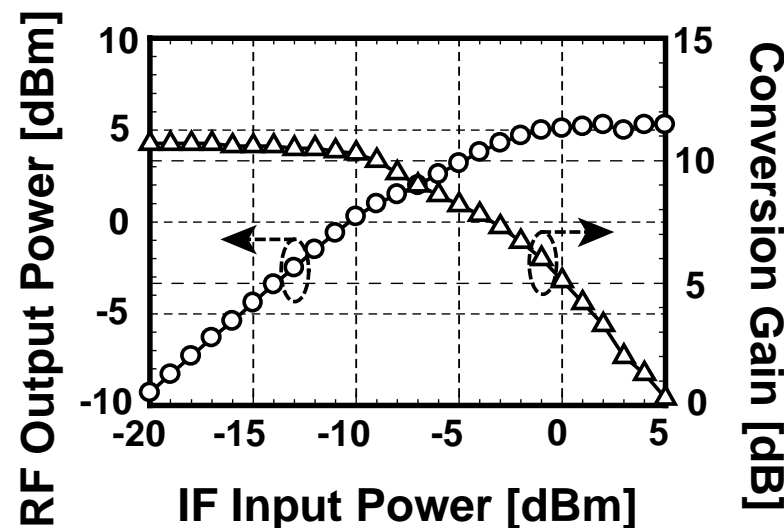


Gain of PA

- **Power Amplifier + Up-conversion Mixer**
 - Passive mixer
 - Diff. IF input, Diff. LO input, Single RF output
- **Measurement results**
 - Conversion Gain : 10.6 [dB]
 - Output Power @ 1dB : 1.6 [dBm]



Chip photo



- I designed a 60GHz Direct-Conversion Transmitter in 65nm CMOS Technology.
- The present device models are not accurate at more than 20GHz, so we built the device models, for example, transistors, capacitors, TLs and de-coupling capacitors by using a new de-embedding method.
- The performance of transmitter(60GHz)
 - Conversion Gain : 10.6 [dB]
 - Output Power @ 1dB : 1.6 [dBm]